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**Thomas I. Wallow
Christoph K. Hohle**
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The CID Number appears on each page of the manuscript. The complete citation is used on the first page, and an abbreviated version on subsequent pages. Numbers in the index correspond to the last two digits of the six-digit CID Number.

Contents

xi *Conference Committee*

NEW EUV RESIST MATERIALS: JOINT SESSION WITH CONFERENCES 9048 AND 9051

- 9051 06 **Novel non-chemically amplified (n-CARs) negative resists for EUVL** [9051-5]
V. Singh, V. S. V. Satyanarayana, S. K. Sharma, S. Ghosh, K. E. Gonsalves, Indian Institute of Technology Mandi (India)
- 9051 07 **Evaluation of vacancies in positive-tone non-chemically and chemically amplified EUV / EB resists: relationship between free-volume and LER** [9051-6]
A. Oshima, Osaka Univ. (Japan) and Waseda Univ. (Japan); T. Hinata, H. Nakamura, Waseda Univ. (Japan); T. Oka, Tohoku Univ. (Japan); N. Oshima, B. E. O'Rourke, R. Suzuki, National Institute of Advanced Industrial Science and Technology (Japan); M. Washio, Waseda Univ. (Japan); S. Tagawa, Osaka Univ. (Japan) and Waseda Univ. (Japan)

STOCHASTICS AND EUV PROCESS IMPROVEMENTS: JOINT SESSION WITH CONFERENCES 9048 AND 9051

- 9051 08 **Manufacturability improvements in EUV resist processing toward NXE:3300 processing** [9051-7]
Y. Kuwahara, K. Matsunaga, T. Shimoaoki, S. Kawakami, K. Nafus, Tokyo Electron Kyushu Ltd. (Japan); P. Foubert, A.-M. Goethals, IMEC (Belgium); S. Shimura, Tokyo Electron Kyushu Ltd. (Japan)

SEM SIMULATION AND EMULATION I: JOINT SESSION WITH CONFERENCES 9050 AND 9051

- 9051 09 **Investigation of interactions between metrology and lithography with a CD SEM simulator** [9051-8]
M. D. Smith, C. Fang, J. J. Biafore, A. Vaglio Pret, S. A. Robertson, KLA-Tencor Corp. (United States)

SEM SIMULATION AND EMULATION II: JOINT SESSION WITH CONFERENCES 9050 AND 9051

- 9051 0A **Assessing SEM contour based OPC models quality using rigorous simulation** [9051-9]
F. Weisbuch, A. Samy Naranaya, GLOBALFOUNDRIES Dresden (Germany)
- 9051 0B **SEM simulation for 2D and 3D inspection metrology and defect review** [9051-10]
S. Levi, I. Schwarzband, S. Khristo, Y. Ivanchenko, O. Adan, Applied Materials, Inc. (Israel)

NEW MATERIALS AND PROCESSES

- 9051 0D **Chiral nanomaterial fabrication by means of on-edge lithography** [9051-12]
K. Dietrich, D. Lehr, O. Puffky, Friedrich-Schiller-Univ. Jena (Germany); E.-B. Kley, A. Tünnermann, Friedrich-Schiller-Univ. Jena (Germany) and Fraunhofer-Institut für Angewandte Optik und Feinmechanik (Germany)
- 9051 0E **Positive tone cross-linked resists based on photoacid inhibition of cross linking** [9051-13]
R. A. Lawson, Georgia Institute of Technology (United States); J. S. Chun, SEMATECH Inc. (United States) and SUNY College of Nanoscale Science and Engineering (United States); M. Neisser, SEMATECH Inc. (United States); L. M. Tolbert, C. L. Henderson, Georgia Institute of Technology (United States)
- 9051 0G **Nanopatterning with tailored molecules** [9051-15]
F. Wieberger, T. Kolb, C. Neuber, Univ. Bayreuth (Germany); C. K. Ober, Cornell Univ. (United States); H.-W. Schmidt, Univ. Bayreuth (Germany)
- 9051 0H **Line width roughness reduction by rational design of photoacid generator for sub-millisecond laser post-exposure bake** [9051-16]
J. Jiang, M. O. Thompson, C. K. Ober, Cornell Univ. (United States)

DSA MATERIALS I

- 9051 0I **Process optimization of templated DSA flows** [9051-17]
R. Gronheid, J. Bekaert, V.-K. Murugesan Kuppuswamy, N. Vandenbroeck, IMEC (Belgium); J. Doise, IMEC (Belgium) and Katholieke Univ. Leuven (Belgium); Y. Cao, G. Lin, AZ Electronic Materials (United States); S. Sayan, Intel Corp. (United States); D. Parnell, M. Somervell, Tokyo Electron America, Inc. (United States)
- 9051 0J **An *in-situ* hard mask block copolymer approach for the fabrication of ordered, large scale, horizontally aligned, Si nanowire arrays on Si substrate** [9051-18]
T. Ghoshal, R. Senthamarai Kannan, Univ. College Cork (Ireland) and Trinity College Dublin (Ireland); M. T. Shaw, Intel Ireland Ltd. (Ireland); J. D. Holmes, M. A. Morris, Univ. College Cork (Ireland) and Trinity College Dublin (Ireland)
- 9051 0K **Investigation of cross-linking poly(methyl methacrylate) as a guiding material in block copolymer directed self-assembly** [9051-19]
R. Seidel, P. Rincon Delgadillo, IMEC (Belgium) and The Univ. of Chicago (United States); A. Ramirez-Hernandez, The Univ. of Chicago (United States); H. Wu, Y. Her, J. Yin, AZ Electronic Materials USA Corp. (United States); P. Nealey, J. de Pablo, The Univ. of Chicago (United States); R. Gronheid, IMEC (Belgium)
- 9051 0L **Novel surface treatment materials for aligning block-co-polymer in directed self-assembly processes** [9051-20]
Y. Someya, H. Wakayama, T. Endo, R. Sakamoto, Nissan Chemical Industries, Ltd. (Japan)

- 9051 OM **Directed self-assembly process integration: Fin patterning approaches and challenges** [9051-21]
S. Sayan, Intel Corp. (United States) and IMEC (Belgium); B. T. Chan, R. Gronheid, F. Van Roey, M.-S. Kim, IMEC (Belgium); L. Williamson, IMEC (Belgium) and The Univ. of Chicago (United States); P. Nealey, The Univ. of Chicago (United States)

DSA MATERIALS AND PROCESSES I: JOINT SESSION WITH CONFERENCES 9049 AND 9051

- 9051 ON **High-volume manufacturing equipment and processing for directed self-assembly applications (Invited Paper)** [9051-22]
M. Somervell, Tokyo Electron America, Inc. (United States); T. Yamauchi, S. Okada, T. Tomita, T. Nishi, Tokyo Electron Kyushu Ltd. (Japan); E. Iijima, Tokyo Electron Miyagi Ltd. (Japan); T. Nakano, T. Ishiguro, S. Nagahara, H. Iwaki, M. Dojun, M. Ozawa, K. Yatsuda, T. Tobana, Tokyo Electron Ltd. (Japan); A. Romo Negreira, Tokyo Electron Ltd. (Belgium); D. Parnell, Tokyo Electron Europe Ltd. (Netherlands); S. Kawakami, M. Muramatsu, Tokyo Electron Kyushu Ltd. (Japan); B. Rath sack, Tokyo Electron America, Inc. (United States); K. Nafus, Tokyo Electron Ltd. (Belgium); J.-L. Peyre, Tokyo Electron Europe Ltd. (France); T. Kitano, Tokyo Electron Kyushu Ltd. (Japan)

MATERIALS AND PROCESS FUNDAMENTALS

- 9051 OO **An in situ analysis of resist dissolution in alkali-based and organic solvent-based developers using high speed atomic force microscopy** [9051-23]
J. J. Santillan, M. Shichiri, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 9051 OP **In-situ analysis of defect formation in coat develop track process** [9051-24]
M. Harumoto, Dainippon Screen Manufacturing Co., Ltd. (Japan); H. Stokes, Dainippon Screen Deutschland GmbH (Germany); O. Tamada, T. Miyagi, K. Kaneyama, Dainippon Screen Manufacturing Co., Ltd. (Japan); C. Pieczulewski, SOKUDO Co., Ltd. (Japan); M. Asai, Dainippon Screen Manufacturing Co., Ltd. (Japan)
- 9051 OQ **Methods of controlling cross-linking in negative-tone resists** [9051-25]
R. A. Lawson, Georgia Institute of Technology (United States); J. S. Chun, SEMATECH Inc. (United States) and SUNY College of Nanoscale Science and Engineering (United States); M. Neisser, SEMATECH Inc. (United States); L. M. Tolbert, C. L. Henderson, Georgia Institute of Technology (United States)
- 9051 OR **How to design a good photoresist solvent package using solubility parameters and high-throughput research** [9051-26]
M. P. Tate, C. Cutler, M. Sakillaris, M. Kaufman, T. Estelle, C. Mohler, C. Tucker, J. Thackeray, The Dow Chemical Co. (United States)
- 9051 OS **ICE: Ionic contrast enhancement for organic solvent negative tone develop** [9051-27]
L. K. Sundberg, G. M. Wallraff, L. D. Bozano, H. D. Truong, M. I. Sanchez, IBM Almaden Research Ctr. (United States); D. L. Goldfarb, IBM Thomas J. Watson Research Ctr. (United States); K. E. Petrillo, IBM Systems and Technology Group (United States); W. D. Hinsberg, Columbia Technical Consulting, Inc. (United States)

- 9051 OT **Introduction of an innovative water based photoresist stripping process using intelligent fluids** [9051-28]
M. Rudolph, X. Thrun, Fraunhofer-Institut für Photonische Mikrosysteme (Germany);
D. Schumann, A. Höhne, S. Esche, bubbles and beyond GmbH (Germany); C. Hohle,
Fraunhofer-Institut für Photonische Mikrosysteme (Germany)

ADVANCED PATTERNING PROCESSES

- 9051 OU **Reduction of image placement error on photomask-making for multiple patterning** [9051-29]
T. Hiromatsu, T. Fukui, K. Tsukagoshi, K. Ono, M. Hashimoto, HOYA Corp. (Japan)
- 9051 OV **Robust complementary technique with multiple-patterning for sub-10 nm node device** [9051-30]
K. Oyama, S. Yamauchi, S. Natori, A. Hara, M. Yamato, H. Yaegashi, Tokyo Electron Ltd. (Japan)
- 9051 OW **Advanced develop processes for reducing defects related with e-beam resists** [9051-31]
B. Lee, S.-J. Han, S.-G. Moon, H. B. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 9051 OX **Recent progress on multiple-patterning process** [9051-33]
H. Yaegashi, K. Oyama, A. Hara, S. Natori, S. Yamauchi, M. Yamato, Tokyo Electron Ltd. (Japan)
- 9051 OY **Novel and cost-effective multiple patterning technology by means of invisible SiO_xN_y hardmask** [9051-34]
L. Jang, Y. J. Moon, R.-H. Kim, GLOBALFOUNDRIES Inc. (United States); C. Bencher, H. Dai, P. Xie, D. L. Diehl, Y. Cao, W. Zeng, C. S. Ngai, Applied Materials, Inc. (United States)

DSA MATERIALS II

- 9051 OZ **Manufacturability considerations for DSA** [9051-35]
R. A. Farrell, E. R. Hosler, G. M. Schmid, J. Xu, M. E. Preil, GLOBALFOUNDRIES Inc. (United States); V. Rastogi, N. Mohanty, K. Kumar, M. J. Cicoria, D. R. Hetzer, A. J. DeVilliers, TEL Technology Ctr., America, LLC (United States)
- 9051 10 **Formation of sub-7 nm feature size PS-b-P4VP block copolymer structures by solvent vapour process** [9051-36]
A. Chaudhari, T. Ghoshal, Univ. College Cork (Ireland) and Trinity College Dublin (Ireland); M. T. Shaw, Univ. College Cork (Ireland), Trinity College Dublin (Ireland), and Intel Ireland Ltd. (Ireland); C. Cummins, D. Borah, J. D. Holmes, M. A. Morris, Univ. College Cork (Ireland) and Trinity College Dublin (Ireland)
- 9051 11 **New materials for directed self-assembly for advanced patterning** [9051-37]
J. Zhang, J. Wu, M. Li, Dow Electronic Materials (United States); V. V. Ginzburg, J. D. Weinhold, M. B. Clark, The Dow Chemical Co. (United States); P. Trefonas III, P. D. Hustad, Dow Electronic Materials (United States)

UNDERLAYERS AND SPIN-ON MATERIALS PROCESSING

- 9051 14 **Extending lithography with advanced materials (Invited Paper)** [9051-40]
D. J. Guerrero, Brewer Science, Inc. (United States)
- 9051 15 **Spin-on organic hardmask for topo-patterned substrate** [9051-41]
K. Komura, Y. Hishiro, JSR Micro, Inc. (United States); G. Wakamatsu, Y. Takimoto, T. Nagai, T. Kimura, Y. Yamaguchi, T. Shimokawa, JSR Corp. (Japan); G. Breyta, N. Arellano, S. Balakrishnan, L. D. Bozano, A. Sankaranarayanan, K. M. Bajjuri, D. P. Sanders, C. E. Larson, IBM Almaden Research Ctr. (United States); A. DeSilva, IBM Corp. (United States); M. Glodde, IBM Thomas J. Watson Research Ctr. (United States)
- 9051 16 **EUV lithography and etching performance enhancement by EUV sensitive Si hard mask (EUV Si-HM) for 1Xnm hp generation** [9051-42]
W. Shibayama, S. Shigaki, N. Fujitani, R. Onishi, R. Sakamoto, Nissan Chemical Industries, Ltd. (Japan)
- 9051 17 **A chemical underlayer approach to mitigate shot noise in EUV contact hole patterning** [9051-44]
J. Li, I. Yasuaki, S. Nakasugi, M. Misumi, H. Yanagita, F. Suzuki, G. Pawlowski, AZ Electronic Materials Manufacturing (Japan); J. Cho, H. Yao, T. Kudo, M. Padmanaban, Y. Her, Y. Cao, AZ Electronic Materials (United States)
- 9051 18 **Anti-spacer double patterning** [9051-45]
M. Hyatt, Micron Technology, Inc. (United States); K. Huang, JSR Micro, Inc. (United States); A. DeVilliers, Tokyo Electron America, Inc. (United States); M. Slezak, Z. Liu, JSR Micro, Inc. (United States)

EUV MATERIALS

- 9051 19 **Optimization of fullerene-based negative tone chemically amplified fullerene resist for extreme ultraviolet lithography** [9051-46]
A. Frommhold, D. X. Yang, The Univ. of Birmingham (United Kingdom); A. McClelland, Irresistible Materials Ltd. (United Kingdom); X. Xue, Nano-C, Inc. (United States); Y. Ekinci, Paul Scherrer Institut (Switzerland); R. E. Palmer, A. P. G. Robinson, The Univ. of Birmingham (United Kingdom)
- 9051 1A **Patterning chemistry of HfSO_x resist** [9051-47]
J. M. Amador, S. R. Decker, S. E. Lucchini, R. E. Ruther, D. A. Keszler, Oregon State Univ. (United States)
- 9051 1B **EUV resists based on tin-oxo clusters** [9051-48]
B. Cardineau, R. Del Re, SUNY College of Nanoscale Science and Engineering (United States); H. Al-Mashat, M. Marnell, State Univ. of New York at New Paltz (United States); M. Vockenhuber, Y. Ekinci, Paul Scherrer Institut (Switzerland); C. Sarma, M. Neisser, SEMATECH Inc. (United States); D. A. Freedman, State Univ. of New York at New Paltz (United States); R. L. Brainard, SUNY College of Nanoscale Science and Engineering (United States)

- 9051 1C **Inhomogeneity of PAGs in resist film studied by molecular-dynamics simulations for EUV lithography** [9051-49]

M. Toriumi, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)

POSTER SESSION: ADVANCED PATTERNING PROCESSES

- 9051 1E **Innovative solutions on 193 immersion-based self-aligned multiple patterning** [9051-52]
S. Natori, S. Yamauchi, A. Hara, M. Yamato, K. Oyama, H. Yaegashi, Tokyo Electron Ltd. (Japan)

- 9051 1F **Wet particle source identification and reduction using a new filter cleaning process** [9051-53]
T. Umeda, Nihon Pall Ltd. (Japan); A. Morita, H. Shimizu, Dainippon Screen Manufacturing Co., Ltd. (Japan); S. Tsuzuki, Nihon Pall Ltd. (Japan)

- 9051 1G **Adsorption characteristics of lithography filters in various solvents using application-specific ratings** [9051-54]
T. Umeda, S. Tsuzuki, Nihon Pall Ltd. (Japan)

- 9051 1H **Removal of highly crosslinked resists and hybrid polymers for single micro parts fabrication and nanoimprint stamp rework** [9051-56]
A. Voigt, R. Engelke, G. Ahrens, F. Bullerjahn, A. Schleunitz, J. J. Klein, G. Gruetzner, micro resist technology GmbH (Germany)

- 9051 1J **Characterization of chemically amplified resists for electron beam lithography** [9051-58]
T. Yamazaki, H. Yamamoto, T. Kozawa, Osaka Univ. (Japan); W.-C. Wang, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)

- 9051 1K **Improved adhesion of novolac and epoxy based resists by cationic organic materials on critical substrates for high volume patterning applications** [9051-59]
A. Voigt, G. Ahrens, M. Heinrich, micro resist technology GmbH (Germany); A. Thompson, DisChem, Inc. (United States); G. Gruetzner, micro resist technology GmbH (Germany)

POSTER SESSION: MATERIALS AND PROCESS FUNDAMENTALS

- 9051 1L **Spin on lithographic resist trim process optimization and process window evaluation** [9051-43]
C. F. Karanikas, GLOBALFOUNDRIES Inc. (United States); J. C. Taylor, The Dow Chemical Co. (United States); N. Vaduri, T. Islam, GLOBALFOUNDRIES Inc. (United States)

- 9051 1M **Modeling acid transport in chemically amplified resist films** [9051-60]
A. A. Patil, M. Doxastakis, G. E. Stein, Univ. of Houston (United States)

- 9051 1O **Deprotonation mechanism of ionized poly(4-hydroxystyrene)** [9051-62]
T. Susa, K. Okamoto, T. Ishida, Hokkaido Univ. (Japan); H. Yamamoto, T. Kozawa, Osaka Univ. (Japan); R. Fujiyoshi, K. Umegaki, Hokkaido Univ. (Japan)

- 9051 1P **Numerical analysis for resist profile after thermal process in display manufacturing** [9051-63]
V. Domnenko, Synopsys SPb, LLC (Russian Federation); H.-J. Stock, Synopsys GmbH (Germany); S. Shin, J. Ryu, S. W. Choi, H. Cho, Samsung Display Co., Ltd. (Korea, Republic of); E.-S. Jeong, J.-H. Choi, Synopsys Korea, Inc. (Korea, Republic of)
- 9051 1Q **Photoresist analysis to investigate LWR generation mechanism** [9051-64]
K. Mochida, S. Nakamura, T. Kimura, JSR Corp. (Japan); K. Kawai, Y. Taguchi, N. Man, H. Hashimoto, Toray Research Ctr. (Japan)
- 9051 1R **Decreasing curing temperature of spin-on dielectrics by using additives** [9051-65]
J. H. Bae, K. W. Han, E. S. Park, H. C. Yoon, Y. H. Na, J. W. Seo, W. H. Lim, B. S. Kim, J. Y. Jang, Y. Cho, Cheil Industries Inc. (Korea, Republic of)
- 9051 1S **Study of acid diffusion behaves form PAG by using top coat method** [9051-67]
A. Sekiguchi, Y. Matsumoto, Litho Tech Japan Corp. (Japan)
- 9051 1T **Fluidity dependence of deprotonation kinetics of chemically amplified resist** [9051-68]
K. Okamoto, T. Ishida, Hokkaido Univ. (Japan); H. Yamamoto, T. Kozawa, Osaka Univ. (Japan); R. Fujiyoshi, K. Umegaki, Hokkaido Univ. (Japan)

POSTER SESSION: NEW MATERIALS AND PROCESSES

- 9051 1U **Inorganic resist materials based on zirconium phosphonate for atomic force microscope lithography** [9051-69]
M. Kang, Hanyang Univ. (Korea, Republic of) and SAMSUNG Electronics Co., Ltd. (Korea, Republic of); S. Kim, J. Jung, Hanyang Univ. (Korea, Republic of); H. Kim, I. Shin, C. Jeon, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); H. Lee, Hanyang Univ. (Korea, Republic of)
- 9051 1W **Organic-inorganic hybrid resists for EUVL** [9051-71]
V. Singh, V. Kalyani, V. S. V. Satyanarayana, C. P. Pradeep, S. Ghosh, S. Sharma, Indian Institute of Technology Mandi (India); K. E. Gonsalves, Indian Institute of Technology Mandi (India) and The Univ. of North Carolina at Charlotte (United States)
- 9051 1X **Development of spin-on-carbon hard mask for advanced node** [9051-72]
T. Kudo, M. D. Rahman, D. McKenzie, C. Anyadiegwu, AZ Electronic Materials USA Corp. (United States); S. Doerrenbaecher, W. Zahn, AZ Electronic Materials Germany GmbH (Germany); M. Padmanaban, AZ Electronic Materials USA Corp. (United States)
- 9051 1Y **Effective resist profile control** [9051-73]
C.-Y. Liu, C.-W. Wang, C.-C. Huang, C.-Y. Chang, Y.-C. Ku, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
- 9051 1Z **Study on resist performance of chemically amplified molecular resist based on noria derivative and calixarene derivative** [9051-74]
H. Yamamoto, Osaka Univ. (Japan); H. Kudo, Kansai Univ. (Japan); T. Kozawa, Osaka Univ. (Japan)
- 9051 20 **SRAF window improvement with under-coating layer** [9051-76]
T. Hiromatsu, T. Fukui, K. Tsukagoshi, K. Ono, M. Hashimoto, HOYA Corp. (Japan)

- 9051 21 **Development of new xanthendiol derivatives applied to the negative-tone molecular resists for EB/EUVL** [9051-77]
T. Sato, M. Yamakawa, Y. Ochiai, Y. Okada, T. Makinoshima, M. Takasuka, M. Echigo, Mitsubishi Gas Chemical Co., Inc. (Japan)
- 9051 23 **Chemical shrink materials and process for negative tone development (NTD) resist** [9051-79]
Y. Miyamoto, AZ Electronic Materials Manufacturing K.K. (Japan); J. Sagan, M. Padmanaban, AZ Electronic Materials USA Corp. (United States); G. Pawlowski, T. Nagahara, AZ Electronic Materials Manufacturing K.K. (Japan)
- 9051 24 **Novel polymeric sulfonium photoacid generator and its application for chemically amplified photoresists** [9051-80]
J. Liu, Y. Qiao, L. Wang, Beijing Normal Univ. (China)
- 9051 25 **Evaluation of novel hydrophilic derivatives for chemically amplified EUV resists** [9051-81]
H. Tanagi, H. Tanaka, S. Hayakawa, K. Furukawa, Mitsubishi Gas Chemical Co., Inc. (Japan); H. Yamamoto, T. Kozawa, Osaka Univ. (Japan)
- 9051 26 **ArF photoresist polymers with nitrogen or sulfone moieties for negative tone development process** [9051-82]
D.-G. Kim, S.-J. Kwon, Seoul National Univ. (Korea, Republic of); S.-K. Hong, J. J. Lee, H. R. Lee, H. J. Yun, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); J.-H. Baik, Seoul National Univ. (Korea, Republic of); D. Im, E. Jang, J.-W. Lee, J.-H. Kim, Dongjin Semichem Co., Ltd. (Korea, Republic of); J.-C. Lee, Seoul National Univ. (Korea, Republic of)
- 9051 27 **Development of novel protecting derivatives for chemically amplified extreme ultraviolet resist** [9051-83]
H. Tanaka, H. Tanagi, S. Hayakawa, K. Furukawa, Mitsubishi Gas Chemical Co., Inc. (Japan); H. Yamamoto, T. Kozawa, Osaka Univ. (Japan)
- 9051 2A **EUV resists comprised of main group organometallic oligomeric materials** [9051-86]
J. Passarelli, B. Cardineau, R. Del Re, M. Sortland, SUNY College of Nanoscale Science and Engineering (United States); M. Vockenhuber, Y. Ekin, Paul Scherrer Institut (Switzerland); C. Sarma, M. Neisser, SEMATECH Inc. (United States); D. A. Freedman, State Univ. of New York at New Paltz (United States); R. L. Brainard, SUNY College of Nanoscale Science and Engineering (United States)

POSTER SESSION: UNDERLAYERS AND SPIN-ON MATERIALS PROCESSING

- 9051 2B **Novel spin-on metal hardmask materials for filling applications** [9051-87]
A. D. Diones, V. Chada, E. Wolfer, E. Ng, S. Mullen, H. Yao, J. Cho, M. Padmanaban, AZ Electronic Materials USA Corp. (United States)

Author Index

Conference Committee

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Roel Gronheid, IMEC (Belgium)
Douglas Guerrero, Brewer Science, Inc. (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)
Scott W. Jessen, Texas Instruments Inc. (United States)
Yoshio Kawai, Shin-Etsu Chemical Co., Ltd. (Japan)
Qinghuang Lin, IBM Thomas J. Watson Research Center
(United States)
Nobuyuki N. Matsuzawa, Sony Corporation (Japan)
Dah-Chung Owe-Yang, Shin-Etsu MicroSi, Inc. (United States)
Daniel P. Sanders, IBM Almaden Research Center (United States)
Mark H. Somervell, Tokyo Electron America, Inc. (United States)
James W. Thackeray, Dow Electronic Materials (United States)
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc.
(United States)
Todd R. Yountin, Intel Corporation (Belgium)

Session Chairs

- 1 Keynote Session
Thomas I. Wallow, ASML US, Inc. (United States)
Christoph K. Hohle, Fraunhofer Institute for Photonics Microsystems
IPMS (Germany)
- 2 New EUV Resist Materials: Joint Session with Conferences 9048 and
9051
Robert L. Brainard, College of Nanoscale Science & Engineering,
University at Albany (United States)
James W. Thackeray, Dow Electronic Materials (United States)
- 3 Stochastics and EUV Process Improvements: Joint Session with
Conferences 9048 and 9051
Roel Gronheid, IMEC (Belgium)
Uzodinma Okoroanyanwu, GLOBALFOUNDRIES Inc. (Germany)
- 4 SEM Simulation and Emulation I: Joint Session with Conferences 9050
and 9051
Shunsuke Koshihara, Hitachi High-Technologies Corporation (Japan)
Thomas I. Wallow, ASML US, Inc. (United States)
- 5 SEM Simulation and Emulation II: Joint Session with Conferences 9050
and 9051
Benjamin D. Bunday, SEMATECH Inc. (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)
- 6 New Materials and Processes
Robert Allen, IBM Almaden Research Center (United States)
Ramakrishnan Ayothi, JSR Micro, Inc. (United States)
- 7 DSA Materials I
Ralph R. Dammel, AZ Electronic Materials USA Corporation
(United States)
Douglas Guerrero, Brewer Science, Inc. (United States)
- 8 DSA Materials and Processes I: Joint Session with Conferences 9049
and 9051
Benjamin M. Rath sack, Tokyo Electron America, Inc. (United States)
Roel Gronheid, IMEC (Belgium)
- 9 DSA Materials and Processes II: Joint Session with 9049 and 9051
James A. Liddle, National Institute of Standards and Technology
(United States)
Sean D. Burns, IBM Corporation (United States)

- 10 Materials and Process Fundamentals
Todd R. Younkin, Intel Corporation (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)
- 11 Advanced Patterning Processes
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc.
(United States)
Douglas Guerrero, Brewer Science, Inc. (United States)
- 12 DSA Materials II
Mark H. Somervell, Tokyo Electron America, Inc. (United States)
Daniel P. Sanders, IBM Almaden Research Center (United States)
- 13 Underlayers and Spin-on Materials Processing
Robert Allen, IBM Almaden Research Center (United States)
Christoph K. Hohle, Fraunhofer Institute for Photonic Microsystems
IPMS (Germany)
- 14 EUV Materials
Scott W. Jessen, Texas Instruments Inc. (United States)
Thomas I. Wallow, ASML US, Inc. (United States)